PMEG6020ETR

High-temperature 60 V, 2 A Schottky barrier rectifier **11 October 2012 Product data sheet**

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Average forward current: $I_{F(AV)} \le 2 A$
- Reverse voltage: V_R ≤ 60 V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T_i ≤ 175 °C

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|-------------------------|---|-----|-----|-----|-----|------|
| I _F | forward current | T _{sp} = 160 °C | | - | - | 2.8 | Α |
| I _{F(AV)} | average forward current | δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 100 °C; square wave | [1] | - | - | 2 | А |
| | | δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave | | - | - | 2 | А |
| V_R | reverse voltage | T _j = 25 °C | | - | - | 60 | V |
| V _F | forward voltage | I _F = 2 A; T _j = 25 °C | | - | 460 | 530 | mV |
| I _R | reverse current | T_j = 25 °C; V_R = 60 V; $t_p \le$ 300 µs; $\delta \le$ 0.02 ; pulsed | | - | 60 | 150 | μA |





| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|--|-----|-----|-----|------|
| t _{rr} | reverse recovery time | $I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ | - | 8.5 | - | ns |
| | | T _j = 25 °C | | | | |

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | K | cathode[1] | 1 2 | 1 - 2 |
| 2 | А | anode | SOD123W | sym001 |

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

| Type number | Package | Package | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PMEG6020ETR | SOD123W | plastic surface mounted package; 2 leads | SOD123W | | |

4. Marking

Table 4. Marking codes

| Tubio ii iiiuiiiig oo u oo | |
|----------------------------|--------------|
| Type number | Marking code |
| PMEG6020ETR | EL |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|-----|------|
| V_R | reverse voltage | T _j = 25 °C | | - | 60 | V |
| I _F | forward current | T _{sp} = 160 °C | | - | 2.8 | Α |
| I _{F(AV)} | average forward current | δ = 0.5 ; f = 20 kHz; $T_{amb} \le 100$ °C; square wave | [1] | - | 2 | Α |
| | | δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave | | - | 2 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave | | - | 50 | Α |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|--------------------------|-----|-----|------|------|
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [2] | - | 680 | mW |
| | | | [3] | - | 1150 | mW |
| | | | [1] | - | 2140 | mW |
| T _j | junction temperature | | | - | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |

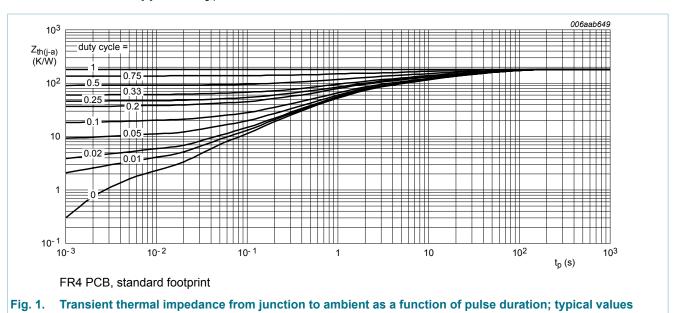
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|--------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance | in free air | [1][2] | - | - | 220 | K/W |
| | from junction to ambient | | [1][3] | - | - | 130 | K/W |
| | ambient | | [1][4] | - | - | 70 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | [5] | - | - | 18 | K/W |

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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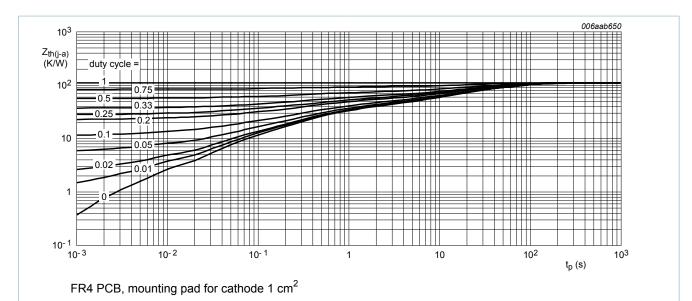
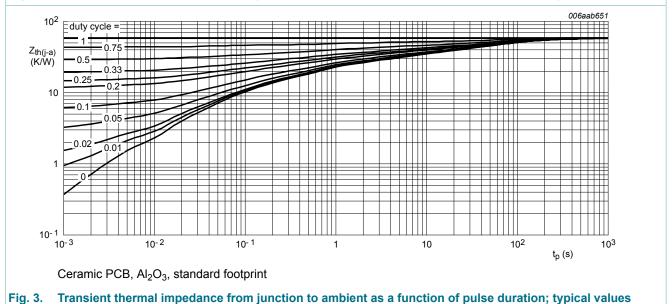


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------------------|--|---|----|-----|-----|---------------|-----------------|
| V _F forward voltage | | I _F = 0.1 A; T _j = 25 °C | | - | 300 | 340 | mV |
| | | I _F = 0.5 A; T _j = 25 °C | | - | 360 | 420 | mV |
| | I _F = 1 A; T _j = 25 °C | | - | 400 | 460 | mV | |
| | | I _F = 1.5 A; T _j = 25 °C | | - | 430 | 500 | mV |
| | | I _F = 2 A; T _j = 25 °C | | - | 460 | 530 | mV |
| | | I _F = 2 A; T _j = -40 °C | | - | 510 | 590 | mV |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|--|-----|-----|-----|------|
| | | I _F = 2 A; T _j = 125 °C | - | 410 | 480 | mV |
| | | I _F = 2 A; T _j = 150 °C | - | 390 | 460 | mV |
| | | I _F = 2 A; T _j = 175 °C | - | 375 | 450 | mV |
| I _R | reverse current | V_R = 5 V; T_j = 25 °C; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; pulsed | - | 2.5 | - | μA |
| | | V_R = 10 V; T_j = 25 °C; $t_p \le$ 300 μs; $\delta \le$ 0.02 ; pulsed | - | 3.5 | - | μA |
| | | V_R = 60 V; T_j = 25 °C; $t_p \le$ 300 μs; $\delta \le$ 0.02 ; pulsed | - | 60 | 150 | μA |
| | | $V_R = 60 \text{ V}; T_j = -40 \text{ °C}; t_p \le 300 \mu\text{s};$ $\delta \le 0.02 \text{ ; pulsed}$ | - | 0.9 | 15 | μA |
| | | V_R = 60 V; T_j = 125 °C; $t_p \le$ 300 μs; $\delta \le$ 0.02 ; pulsed | - | 27 | 100 | mA |
| C _d | diode capacitance | V _R = 1 V; f = 1 MHz; T _j = 25 °C | - | 240 | - | pF |
| | | V _R = 10 V; f = 1 MHz; T _j = 25 °C | - | 80 | - | pF |
| t _{rr} | reverse recovery time | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$ | - | 8.5 | - | ns |
| V_{FRM} | peak forward recovery voltage | $I_F = 1 \text{ A}; dI_F/dt = 40 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$ | - | 455 | - | mV |

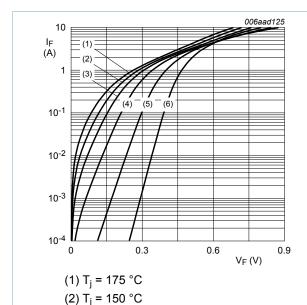


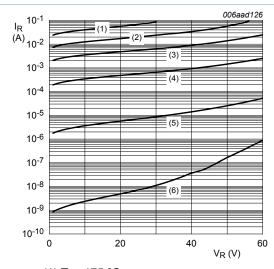
Fig. 4. Forward current as a function of forward voltage; typical values

(3) $T_i = 125 \, ^{\circ}C$

(4) $T_j = 85 \, ^{\circ}C$

(5) $T_i = 25 \, ^{\circ}C$

(6) $T_j = -40 \, ^{\circ}C$



(1) $T_i = 175 \,^{\circ}C$

(2) $T_i = 150 \, ^{\circ}C$

(3) $T_i = 125 \, ^{\circ}C$

(4) $T_j = 85 \, ^{\circ}C$

(5) $T_i = 25 \,{}^{\circ}\text{C}$

(6) $T_j = -40 \, ^{\circ}C$

Fig. 5. Reverse current as a function of reverse voltage; typical values

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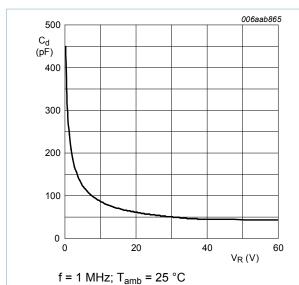
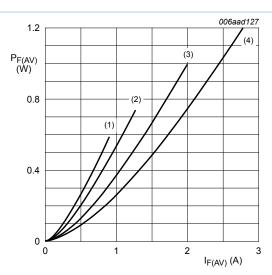
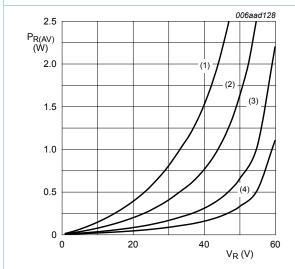


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



 $T_j = 175 \,^{\circ}\text{C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$ (3) $\delta = 0.5$ (4) $\delta = 1$

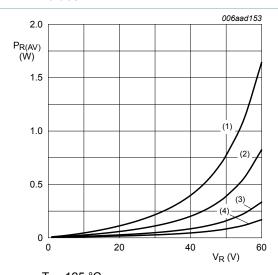
Fig. 7. Average forward power dissipation as a function of average forward current; typical values



 $T_j = 150 \text{ °C}$ (1) $\delta = 1$ (2) $\delta = 0.5$ (3) $\delta = 0.2$

 $(4) \delta = 0.1$

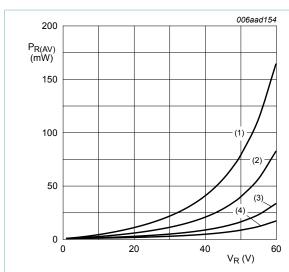
Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



 $T_j = 125 \,^{\circ}\text{C}$ (1) $\delta = 1$ (2) $\delta = 0.5$ (3) $\delta = 0.2$ (4) $\delta = 0.1$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

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 $T_i = 85 °C$

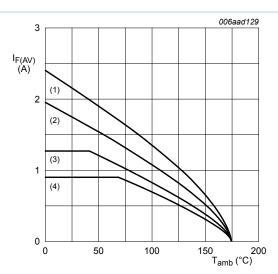
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 175 °C

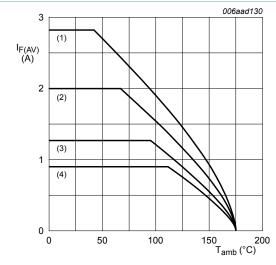
(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 175 °C

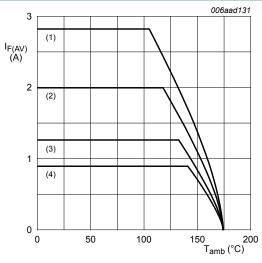
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 175 °C

 $(1) \delta = 1 (DC)$

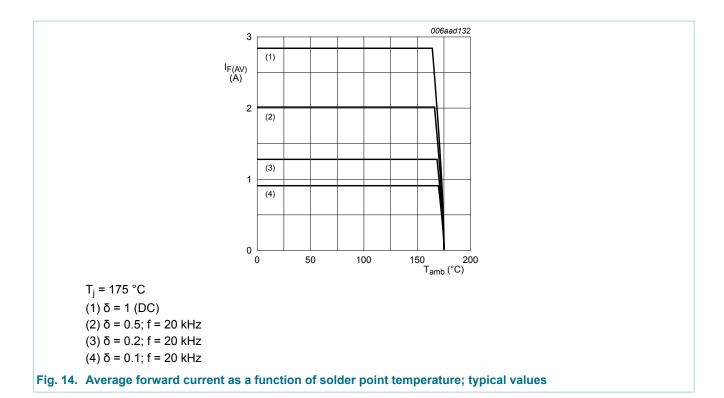
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

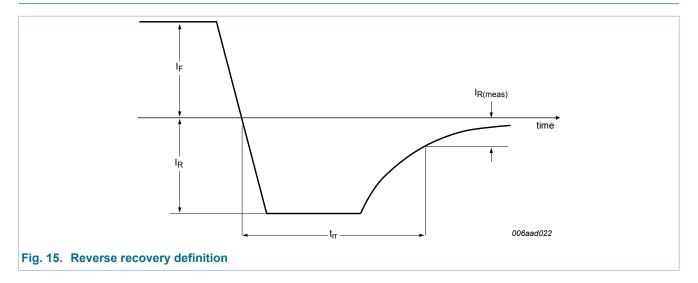
(4) δ = 0.1; f = 20 kHz

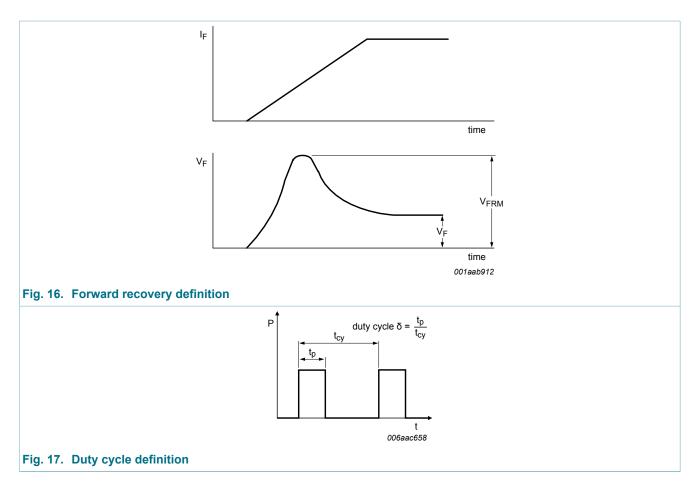
Fig. 13. Average forward current as a function of ambient temperature; typical values

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8. Test information





The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

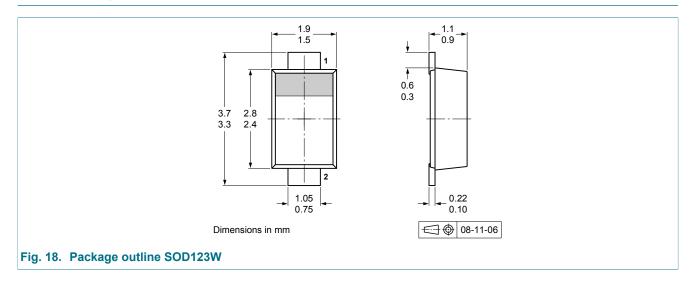
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

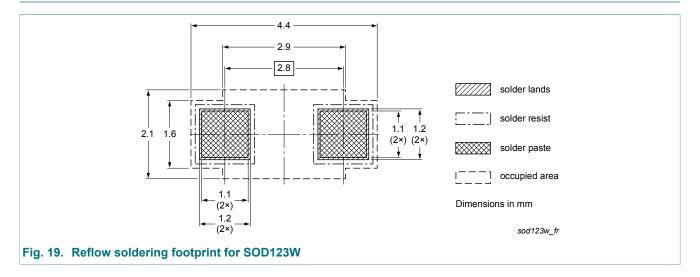
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9. Package outline



10. Soldering



11. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PMEG6020ETR v.1 | 20121011 | Product data sheet | - | - |

12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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